



F. Silicon and Group-IV Devices and Integration Technology 분과

2021년 1월 28일(목), 13:00-14:30 / 채널 B

[TB3-F] Advanced Nano-Device Technology

좌장: 김경록 교수 (UNIST), 이병훈 교수 (POSTECH)

<p>TB3-F-1 13:00-13:30</p>	<p>[초청] Improvement in Self-heating Characteristic by Incorporating Hetero-Gate-Dielectric in Gate-All-Around MOSFET Jang Hyun Kim <i>School of Electrical Engineering, Pukyong National University</i></p>
<p>TB3-F-2 13:30-14:00</p>	<p>[초청] Si Gate-All-Around Nanosheet FET: the Key Enabler of 3nm Technology Node Rock-Hyun Baek <i>Department of Electrical Engineering, POSTECH</i></p>
<p>TB3-F-3 14:00-14:15</p>	<p>Improvement of Self-heating Effect by Effective Heat Sink of Lightly Doped Drain in Asymmetric MOSFET Young Suh Song^{1,2}, and Jang Hyun Kim³ <i>¹Seoul National University, ²Korea Military Academy, ³Pukyong National University</i></p>
<p>TB3-F-4 14:15-14:30</p>	<p>Highly-Scalable and Variation-Immune Fin-Based High Electron Mobility Transistor with Improved RF Characteristics Sung-Ho Kim, Yoo Bin Song, Jong Yul Park, and Kyung Rok Kim <i>Department of Electrical Engineering, UNIST</i></p>